



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	12mΩ @ V _{GS} = 10V	43.3A
60V	15mΩ @ V _{GS} = 4.5V	38.7A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

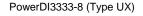
Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

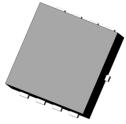
Mechanical Data

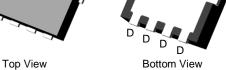
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.030 grams (Approximate)

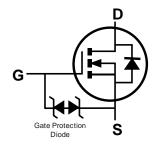
Pin1











Internal Schematic

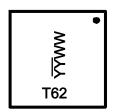
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6012LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape and Reel
DMT6012LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape and Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$		I _D	43.3 34.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	170	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	40	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	170	Α	
Avalanche Current, L = 0.1mH	I _{AS}	23.7	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	28.1	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	1.95	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	64	
Total Power Dissipation (Note 6)	$T_C = +25$ °C	P _D	33.78	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	3.7	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

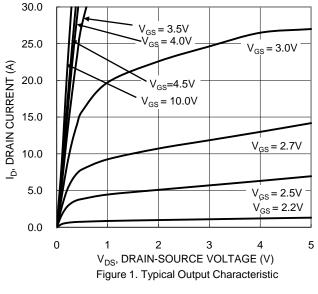
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	8.2	12	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Diani-Source On-Resistance	R _{DS(ON)}		11.2	15		$V_{GS} = 4.5V, I_D = 12.5A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	1522	_		$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	1	352	_	pF		
Reverse Transfer Capacitance	C _{rss}		27.5	_			
Gate Resistance	R_g	-	1.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	10.7	_			
Total Gate Charge (V _{GS} = 10V)	Q_g	_	22.2	_	nC	$V_{DS} = 30V, I_D = 10A$	
Gate-Source Charge	Q_{gs}		3.3	_	IIC		
Gate-Drain Charge	Q_{gd}	_	4.2	_			
Turn-On Delay Time	t _{D(ON)}	_	4.4	_		$V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 6\Omega, I_D = 10A$	
Turn-On Rise Time	t _R	_	6.7	_			
Turn-Off Delay Time	t _{D(OFF)}	-	25.5	_	ns		
Turn-Off Fall Time	t _F	_	12.5	_			
Reverse Recovery Time	t _{RR}	_	25.8	_	ns	1 400 4:/44 4000/	
Reverse Recovery Charge	Q _{RR}	_	15.1	_	nC	I _F = 10A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.





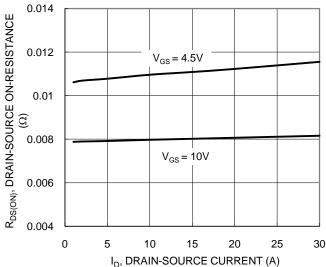


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

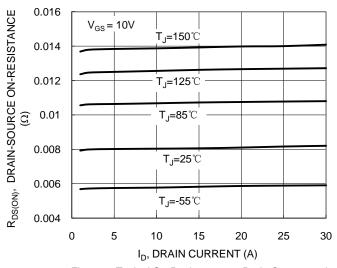


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

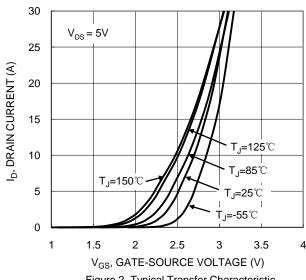


Figure 2. Typical Transfer Characteristic

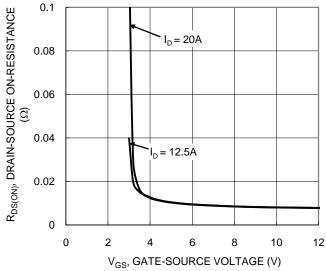


Figure 4. Typical Transfer Characteristic

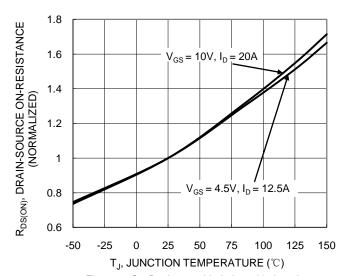


Figure 6. On-Resistance Variation with Junction Temperature



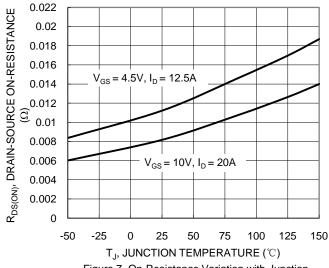


Figure 7. On-Resistance Variation with Junction Temperature

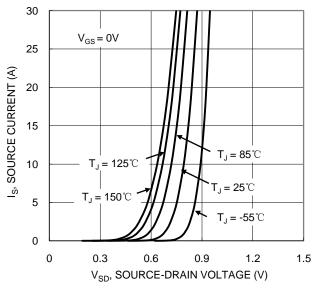


Figure 9. Diode Forward Voltage vs. Current

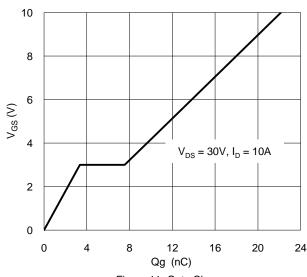


Figure 11. Gate Charge

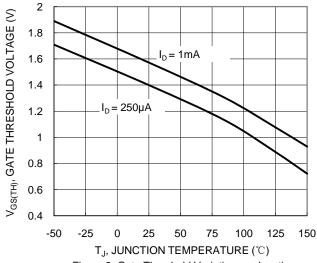
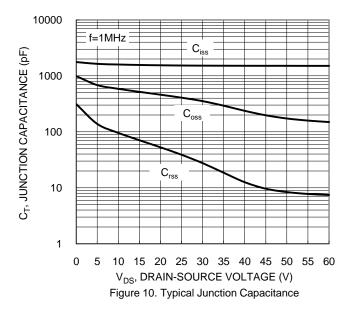


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 $R_{DS(ON)}$ Limited 100 I_D, DRAIN CURRENT (A) 10 P_W =10μs P_W =100μs T_{J(Max)} = 150°C T_C = 25°C Single Pulse $P_W = 100 ms$ 0.1 DUT on Infinite DC Heatsink $V_{GS} = 10V$ 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



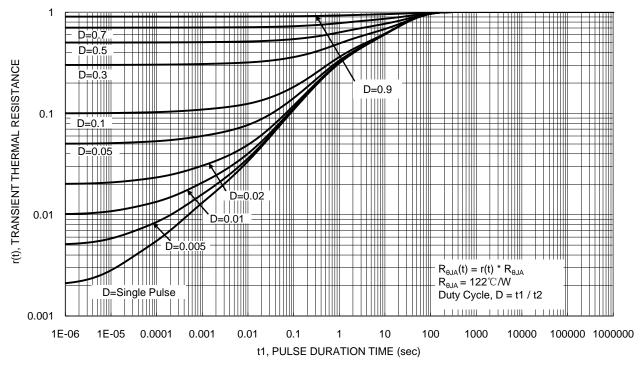


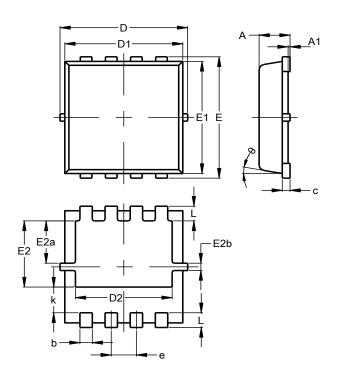
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

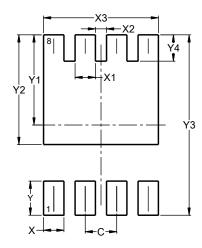


PowerDI3333-8 (Type UX)				
Dim	Min	Тур		
Α	0.75	0.85	0.80	
A1	0.00	0.05		
b	0.25	0.40	0.32	
С	0.10	0.25	0.15	
D	3.20	3.40	3.30	
D1	2.95	3.15	3.05	
D2	2.30	2.70	2.50	
Е	3.20	3.40	3.30	
E1	2.95	3.15	3.05	
E2	1.60	2.00	1.80	
E2a	0.95	1.35	1.15	
E2b	0.10	0.30	0.20	
е	0.65 BSC			
k	0.50	0.90	0.70	
L	0.30	0.50	0.40	
θ	0°	12°	10°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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